

2SD1264, 2SD1264A

Silicon NPN triple diffusion planar type

For low-freQUENCY power amplification

For TV vertical deflection output

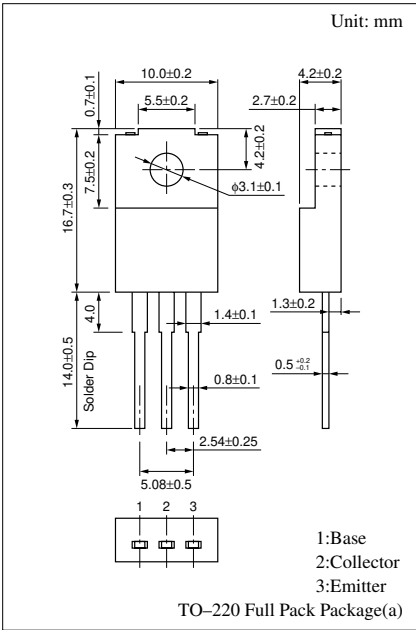
Complementary to 2SB940 and 2SB940A

■ Features

- High collector to emitter V_{CEO}
- Large collector power dissipation P_C
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	200	V
Collector to emitter voltage	2SD1264 2SD1264A	V_{CEO}	V
Emitter to base voltage	V_{EBO}	6	V
Peak collector current	I_{CP}	3	A
Collector current	I_C	2	A
Collector power dissipation	$T_C=25^\circ\text{C}$ $T_a=25^\circ\text{C}$	P_C	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 200\text{V}, I_E = 0$			50	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			50	μA
Collector to base voltage	V_{CBO}	$I_C = 50\mu\text{A}, I_E = 0$	200			V
Collector to emitter voltage	2SD1264 2SD1264A	V_{CEO}	150			V
			180			
Emitter to base voltage	V_{EBO}	$I_E = 500\mu\text{A}, I_C = 0$	6			V
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = 10\text{V}, I_C = 150\text{mA}$	60		240	
	h_{FE2}	$V_{CE} = 10\text{V}, I_C = 400\text{mA}$	50			
Base to emitter voltage	V_{BE}	$V_{CE} = 10\text{V}, I_C = 400\text{mA}$			1	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1	V
Transition frequency	f_T	$V_{CE} = 5\text{V}, I_C = 0.5\text{A}, f = 1\text{MHz}$		20		MHz

* h_{FE1} Rank classification

Rank	Q	P
h_{FE1}	60 to 140	100 to 240

